AMENDMENTS TO THE CLAIMS

Claim 1 (currently amended). A method for manufacturing a SiC device, comprising:

depositing a silicon film above a SiC substrate;

delineating the silicon film into required pattern so as to expose a surface of the SiC substrate; and

annealing the SiC substrate in a water rich ambient to selectively grow a ~~locallized~~ localized thermal oxide film above the SiC substrate.

Claim 2 (original). The method of claim 1, wherein H_2O partial pressure in the water rich ambient is selected such that oxidation rate for the silicon film is larger than that for the SiC substrate.

Claim 3 (original). The method of claim 2, wherein the H_2O partial pressure in the water rich ambient is kept mere than 0.95.

Claim 4 (original). The method of claim 1, wherein said silicon film is delineated into a pattern for an element isolation region.

Claim 5 (currently amended). ~~The~~ A method ~~of claim 1, further~~ for manufacturing a SiC device, comprising:

depositing a silicon film above a SiC substrate;

delineating the silicon film into a required pattern;

annealing the SiC substrate in a water rich ambient to selectively grow a localized thermal oxide film above the SiC substrate;

forming a trench at the surface of the SiC substrate before depositing said silicon film, wherein the silicon film is delineated such that the silicon film buries the trench, and the silicon film buried in the trench is selectively oxidized in the water rich ambient.

Claim 6 (original). The method of claim 1, farther comprising forming a blanket silicon oxide film at the surface of the SiC substrate in an oxygen added ambient, before depositing said silicon film so that said silicon film can deposit on the blanket silicon oxide film.

Claim 7 (original). The method of claim 6, wherein the H_2O partial pressure in the oxygen added ambient is kept less than 0.95.

Claim 8 (original). The method of claim 6, further comprising selectively removing said blanket silicon oxide film using said silicon film as an etching mask so as to expose a part of the surface of the SiC substrate, before said silicon film i3 selectively oxidized in the water rich ambient

Claim 9 (currently amended). ~~The~~ A method ~~of claim 8, further~~ for manufacturing a SiC device, comprising:

forming a blanket silicon oxide film at the surface of the SiC substrate in an oxygen added ambient;

depositing a silicon film on the blanket silicon oxide film;

delineating the silicon film into required pattern;

selectively removing the blanket silicon oxide film using the silicon film as an etching mask so as to expose a part of the surface of the SiC substrate;

annealing the SiC substrate in a water rich ambient to selectively grow a localized thermal oxide film above the SiC substrate; and

forming a thin silicon oxide film at the exposed part of the surface of the SiC substrate in the oxygen added ambient after selectively growing said localized thermal oxide film, wherein the oxygen added ambient and the water rich ambient are successively achieved in a same reaction tube so as not to expose the surface of the SiC substrate to an air outside of the reaction tube.

Claim 10 (original). The method of claim 1, wherein said water rich ambient is achieved by directly introducing ultra pure water in a reaction tube for oxidation.

Claim 11 (currently amended). ~~The~~ A method ~~of claim 8, further~~ for manufacturing a SiC device, comprising:

forming a blanket silicon oxide film at the surface of the SiC substrate in an oxygen added ambient;

depositing a silicon film on the blanket ailicon oxide film;

delineating the silicon film into a required pattern;

selectively removing the blanket silicon oxide film using the silicon film as an etching mask so as to expose a part of the surface of the SiC substrate;

annealing the SiC substrate in a water rich ambient to selectively grow a localized thermal oxide film above the SiC substrate;

forming a gate oxide film at the exposed part of the surface of the SiC substrate in the oxygen added ambient; and

annealing said gate oxide film in the water rich ambient at substrate temperature lower than the substrate temperature at which the gate oxide film is formed.

Claim 12 (original). The method of claim 8, farther comprising:

depositing another silicon film at the exposed part of the surface of the SiC substrate;

annealing the SiC substrate in the water rich ambient to grow a gate oxide film at the exposed part of the surface of the SiC substrate; and

annealing said gate oxide film in the water rich ambient at substrate temperature equal to or lower than the substrate temperature at which the gate oxide film is grown.

Claim 13 (currently amended). A method for manufacturing a SiC device, comprising:

forming a gate oxide film on a surface of a SiC substrate; and

annealing said gate oxide film in a water rich ambient at substrate temperature equal to or lower than the substrate temperature at which the gate oxide film is formed so as to reduce interface density between said gate oxide film and said SiC substrate.

Claim 14 (original). The method of claim 13, wherein H_2O partial pressure in the water rich ambient is kept more than 0.95.

Claim 15 (original). The method of claim 13, wherein said forming the gate oxide film comprising oxidizing the surface of the SiC substrate in an oxygen added ambient.

Claim 16 (original). The method of claim 15, wherein H_2O partial pressure in the oxygen added ambient is kept less than 0.95.

Claim 17 (currently amended). The method of claim 13, wherein said forming the gate oxide film comprising:

depositing a silicon film at the surface of the SiC substrate; and

annealing the SiC substrate in the water rich ambient to grow the gate oxide film at the surface of the SiC substrate.

Claim 18 (original). The method of claim 13, wherein said gate oxide film is annealed at substrate temperature of about 700°C-1050°C.

Claims 19-20 (withdrawn).